



Sub  
B1

4. The semiconductor dynamic sensor as in claim 3,  
wherein:

a thickness of the adhesive film is less than 50  $\mu$   
m.

5. The semiconductor dynamic sensor as in claim 3,  
wherein:

an elasticity coefficient of the adhesive film is  
less than 3,000 mega pascal.

6. The semiconductor dynamic sensor as in claim 1,  
wherein:

the semiconductor sensor chip is a sensor chip for  
sensing acceleration.

7. A method of manufacturing a semiconductor  
dynamic sensor having a semiconductor sensor chip and a  
substrate for mounting the semiconductor sensor chip  
thereon via an adhesive film, the method comprising steps  
of

sticking the adhesive film to a semiconductor wafer  
having a plurality of the sensor chips;

dicing the wafer having a plurality of sensor chips  
together with the adhesive film into individual sensor  
chips; and

connecting the sensor chip to the substrate via the adhesive film.

8. The method of manufacturing a semiconductor dynamic sensor as in claim 7, the method further including a step of coating a surface of the substrate, on which the sensor chip is mounted, with a resin material to smooth the surface.

add  
A'